

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:)
NISHIMOTO et al) Group Art Unit: 2814
Serial No.: 08/897,839) Examiner: K. Eaton
Filed: July 21, 1997)
For: STRESS-ADJUSTED INSULATING)
FILM FORMING METHOD,)
SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING THE)
SAME)

13/Pre
Amatl. B
Shereson
11-29-99



PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Preliminary to examination of the Continuing Prosecution Application (CPA) identified above, please amend the captioned application as follows:

IN THE CLAIMS:

~~Please cancel claims 2-4, 6, 8-14, 16, 17 and 19-32 and add the following new claims:~~

~~--33. A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:~~

~~(a) forming a first insulating layer with a first type of stress;~~